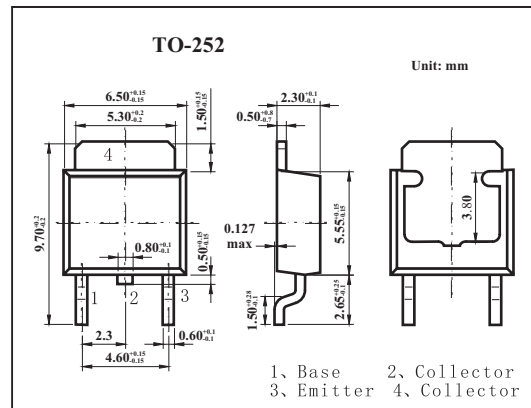


PNP Silicon Triple Diffused Transistor

2SA1400-Z

■ Features

- High Voltage: $V_{CE0} = -400V$
- High Speed: $t_f \leq 1.0\mu s$
- Complement to 2SC3588-Z

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-400	V
Collector-emitter voltage	V_{CE0}	-400	V
Emitter-base voltage	V_{EB0}	-7	V
Collector Current (DC)	I_C	-0.5	A
Collector Current (Pulse) *1	I_C	-1.0	A
Total Power Dissipation ($T_c = 25^\circ C$) *2	P_T	2.0	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

*1 $PW \leq 300\mu s$, Duty Cycle $\leq 10\%$

*2 When mounted on ceramic substrate of $7.5cm^2 \times 0.7mm$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	$V_{CB} = -400V, I_E = 0$			-100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5.0V, I_C = 0$			-10	μA
DC Current Gain	h_{FE}^*	$V_{CE} = -5.0V, I_C = -50mA$	30		200	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}^*$	$I_C = -100mA, I_B = -10mA$			-1.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}^*$	$I_C = -100mA, I_B = -10mA$			1.2	V
Turn-on Time	t_{on}	$V_{CC} \approx -150V, I_C = -100mA$			1.0	μs
Storage Time	t_{stg}	$R_L = 1.5k\Omega$ $I_{B1} = -I_{B2} = -10mA$			5.0	
Fall Time	t_f	$PW \leq 50\mu s, DC \leq 2\%$			1.0	

* Pulsed: $PW \leq 350\mu s$, Duty Cycle $\leq 2\%$

■ h_{FE} Classification

Marking	N	M	L	K
h_{FE}	30 ~ 60	40 ~ 80	60 ~ 120	100 ~ 200